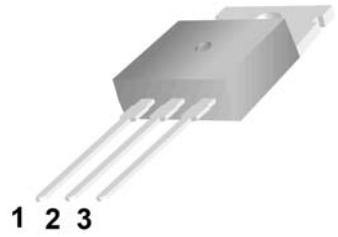
●Features：

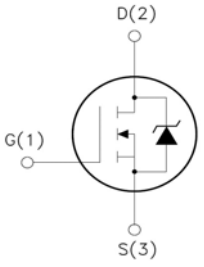
- 4.0A, 550V, $R_{DS(on)(Typ)}$ =2.2Ω@V_{GS}=10V
- Low Gate Charge
- Low C_{rss}
- 100% Avalanche Tested
- Fast Switching
- Improved dv/dt Capability

●Application:

- High Frequency Switching Mode Power Supply
- Active Power Factor Correction



TO-220



1.Gate (G)
2.Drain (D)
3.Source (S)

Absolute Maximum Ratings(Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	550	V
I_D	Drain Current - Continuous(Tc=25°C)	4.0*	A
	- Continuous(Tc=100°C)	2.5*	A
I_{DM}	Drain Current -Pulsed (Note1)	16*	A
V_{GSS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note2)	240	mJ
I_{AR}	Avalanche Current (Note1)	4.0	A
E_{AR}	Repetitive Avalanche Energy (Note1)	10.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	4.5	V/ns
P_D	Power Dissipation(T_C =25°C)	33	W
	-Derate above 25°C	0.26	W/°C
Tj	Operating Junction Temperature	150	°C
Tstg	Storage Temperature Range	-55 to+150	°C

* Drain Current Limited by Maximum Junction Temperature.

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	3.79	°C /W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	62.5	°C /W

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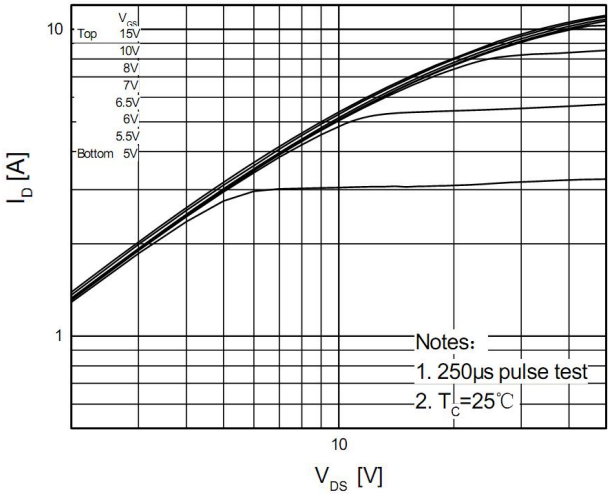
Electrical Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditons	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-source Breakdown Voltage	V_{GS}=0V ,I_D=250μA	550	--	--	V
$\triangle BV_{DSS}$ /$\triangle T_J$	Breakdown Voltage Temperature Coefficient	I_D=250μA (Referenced to 25°C)	--	0.65	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=550V,V_{GS}=0V	--	--	1	μA
		V_{DS}=520V,Tc=125°C	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current,Forward	V_{GS}=+30V, V_{DS}=0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current,Reverse	V_{GS}=-30V, V_{DS}=0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS}=10 V, I_D=2.0A	--	2.2	2.6	Ω
g_{FS}	Forward Transconductance	V_{DS}=40 V, I_D=2.0A (Note4)	--	3.6	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V,V_{GS}=0V, f=1.0MHz	--	560	--	pF
C_{oss}	Output Capacitance		--	62	--	pF
C_{rss}	Reverse Transfer Capacitance		--	10	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 325 V, I_D = 4.0 A, R_G = 25 Ω (Note4,5)	--	30	--	ns
t_r	Turn-On Rise Time		--	75	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	--	ns
t_f	Turn-Off Fall Time		--	55	--	ns
Q_g	Total Gate Charge	V_{DS} = 520 V, I_D =4.0 A, V_{GS} = 10 V (Note4,5)	--	12	--	nC
Q_{gs}	Gate-Source Charge		--	4.0	--	nC
Q_{gd}	Gate-Drain Charge		--	4.8	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	4.0	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	16	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} =0V,I_S=4.0A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} =0V, I_S=4.0A, d I_F /dt=100A/μs (Note4)	--	330	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.67	--	μC

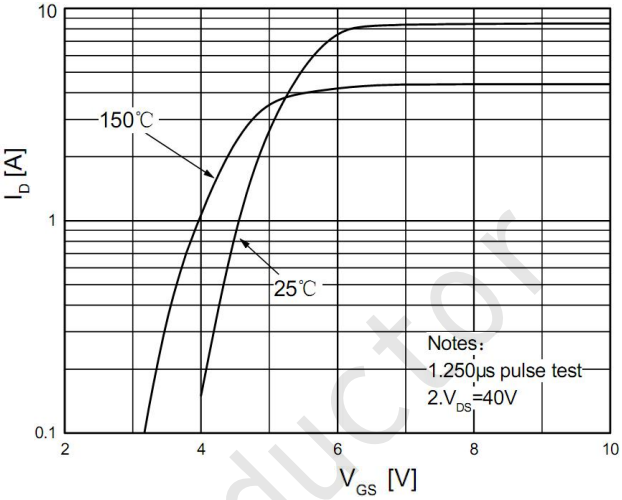
Notes:
1、Repetitive Rating:Pulse Width Limited by Maximum Junction Temperature.
2、L = 25.0mH, I_{AS} =4.0A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C.
3、I_{SD}≤4.0A, di/dt≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J = 25°C.
4、Pulse Test : Pulse Width ≤300 μ s, Duty Cycle≤2%.
5、Essentially Independent of Operating Temperature.

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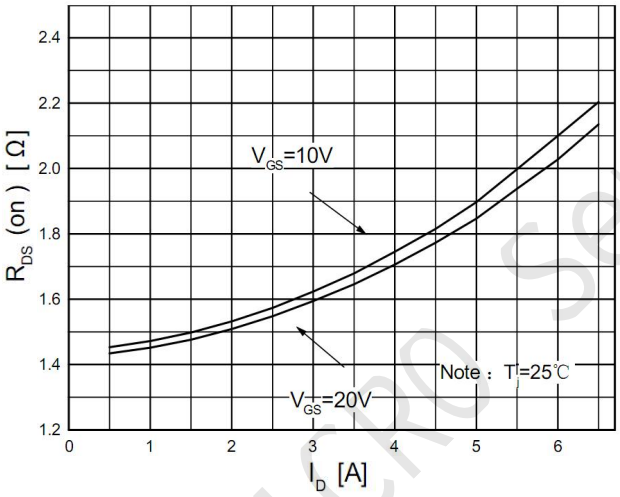
On-Regin Characteristics



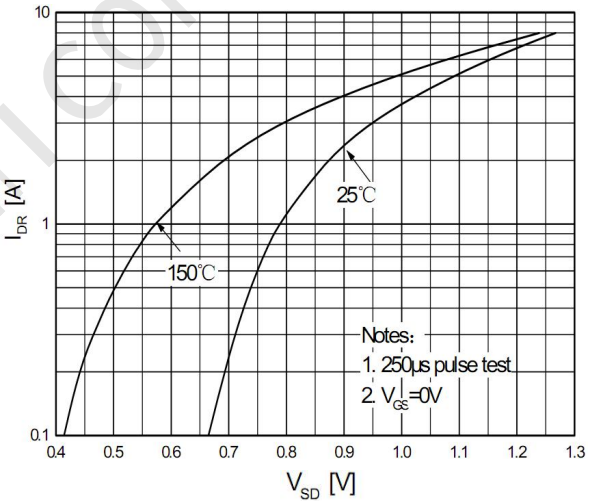
Transfer Characteristics



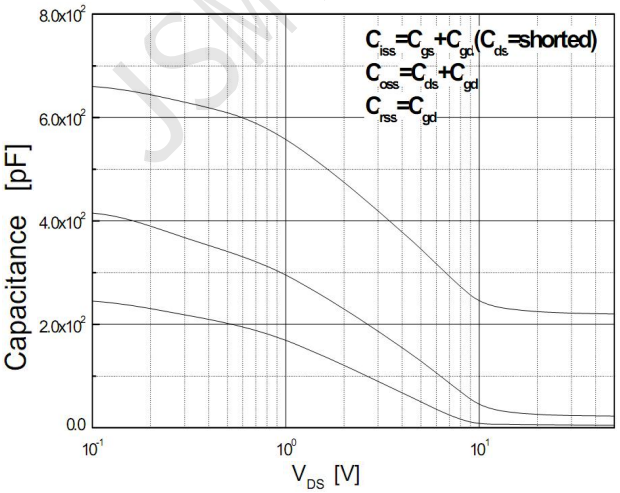
On-Resistance Variation vs. Drain Current and Gate Voltage



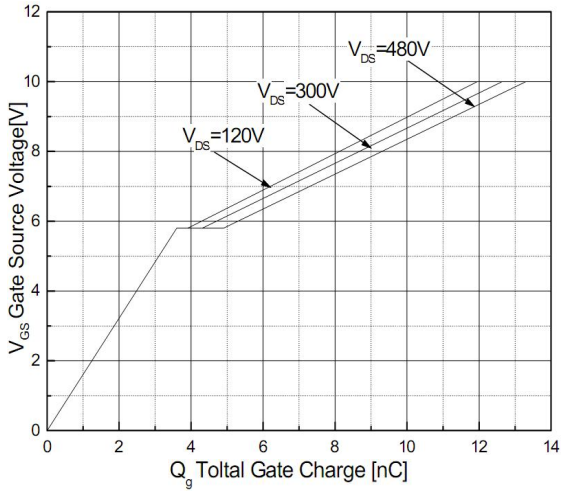
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics

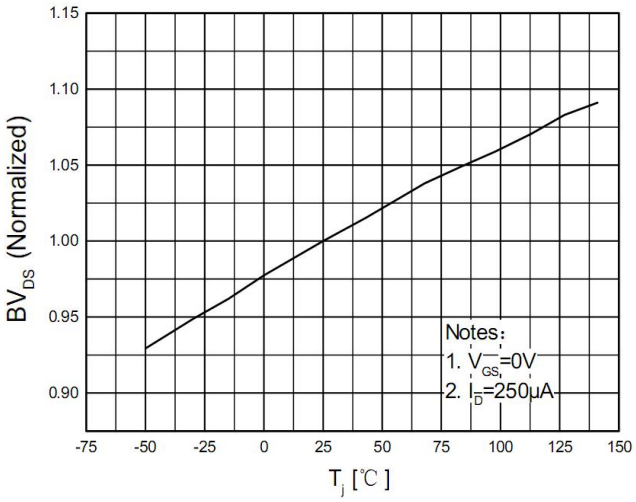


Gate Charge Characteristics

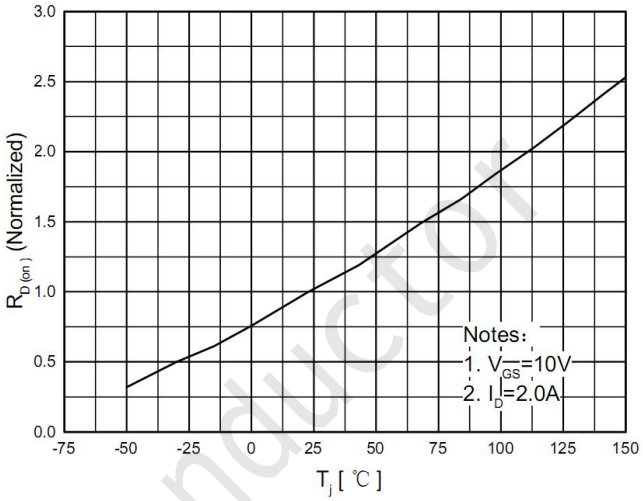


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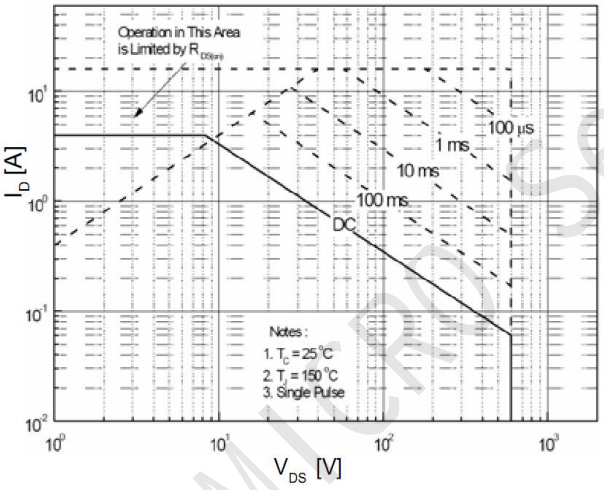
Breakdown Voltage Variation vs. Temperature



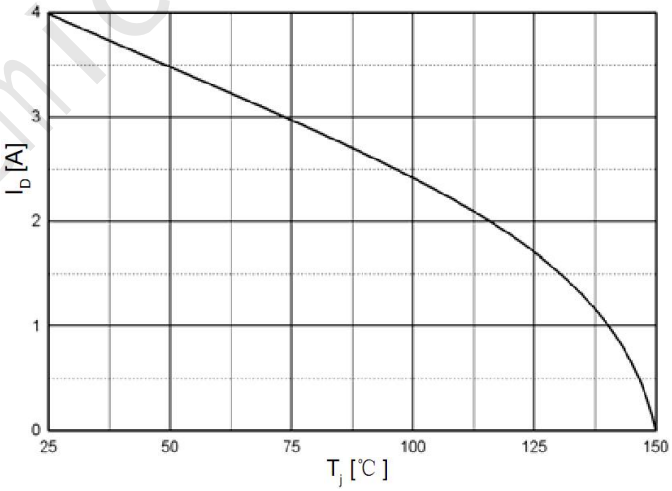
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area

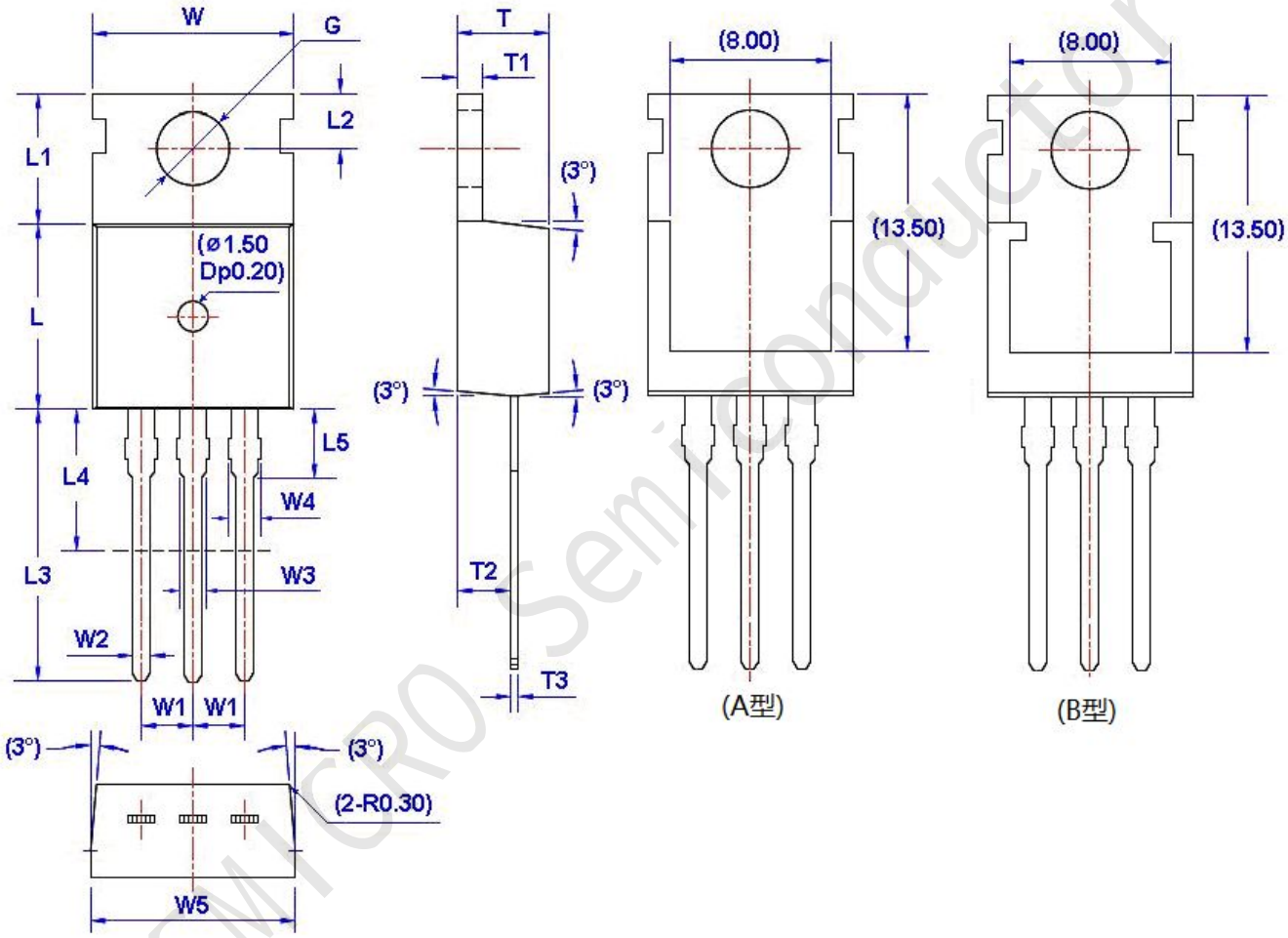


Maximum Drain Current Vs. Case Temperature



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TO-220 Package Dimensions



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Unit: mm

Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.66	10.28	W5	9.80	10.20	L4**	6.20	6.60	T3	0.45	0.60
W1	2.54（TYP）		L	9.00	9.40	L5	2.79	3.30	G(Φ)	3.50	3.70
W2	0.70	0.95	L1	6.40	6.80	T	4.30	4.70			
W3	1.17	1.37	L2	2.70	2.90	T1	1.15	1.40			
W4*	1.32	1.72	L3	12.70	14.27	T2	2.20	2.60			